

Ultrafast recovery - 1200 V diode

Main product characteristics

$I_{F(AV)}$	2 x 30 A
V_{RRM}	1200 V
T_j	150° C
V_F (typ)	1.30 V
t_{rr} (typ)	45 ns

Features and benefits

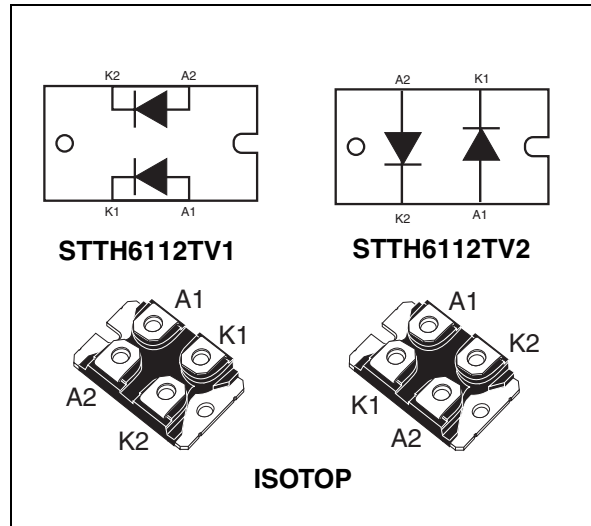
- Ultrafast, soft recovery
- Very low conduction and switching losses
- High frequency and/or high pulsed current operation
- High reverse voltage capability
- High junction temperature
- Insulated package:
Electrical insulation = 2500 V_{RMS}
Capacitance < 45 pF

Description

The high quality design of this diode has produced a device with low leakage current, regularly reproducible characteristics and intrinsic ruggedness. These characteristics make it ideal for heavy duty applications that demand long term reliability.

Such demanding applications include industrial power supplies, motor control, and similar mission-critical systems that require rectification and freewheeling. These diodes also fit into auxiliary functions such as snubber, bootstrap, and demagnetization applications.

The improved performance in low leakage current, and therefore thermal runaway guard band, is an immediate competitive advantage for this device.



Order codes

Part Number	Marking
STTH6112TV1	STTH6112TV1
STTH6112TV2	STTH6112TV2

1 Characteristics

Table 1. Absolute ratings (limiting values per diode at 25° C, unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		1200	V
$I_{F(RMS)}$	RMS forward current		100	A
$I_{F(AV)}$	Average forward current, $\delta = 0.5$	$T_c = 70^\circ \text{C}$ per diode	30	A
I_{FRM}	Repetitive peak forward current	$t_p = 5 \mu\text{s}$, $F = 5 \text{ kHz}$ square	300	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	250	A
T_{stg}	Storage temperature range		-65 to + 150	°C
T_j	Maximum operating junction temperature		150	°C

Table 2. Thermal parameters

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.16	°C/W
		Total	0.63	
$R_{th(c)}$	Coupling thermal resistance		0.1	

When the diodes are used simultaneously:

$$\Delta T_{j(\text{diode1})} = P_{(\text{diode1})} \times R_{th(j-c)} \text{ (per diode)} + P_{(\text{diode2})} \times R_{th(c)}$$

Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25^\circ \text{C}$	$V_R = V_{RRM}$			20	μA
		$T_j = 125^\circ \text{C}$			15	150	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25^\circ \text{C}$	$I_F = 25 \text{ A}$			2.10	V
		$T_j = 125^\circ \text{C}$			1.25	1.90	
		$T_j = 150^\circ \text{C}$			1.20	1.80	
		$T_j = 25^\circ \text{C}$	$I_F = 30 \text{ A}$			2.25	
		$T_j = 125^\circ \text{C}$			1.35	2.05	
		$T_j = 150^\circ \text{C}$			1.30	1.95	

1. Pulse test: $t_p = 5 \text{ ms}$, $\delta < 2 \%$

2. Pulse test: $t_p = 380 \mu\text{s}$, $\delta < 2 \%$

To evaluate the conduction losses use the following equation:

$$P = 1.60 \times I_{F(AV)} + 0.012 I_{F(RMS)}^2$$

Table 4. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ	Max.	Unit
t_{rr}	Reverse recovery time	$I_F = 1\text{ A}$, $di_F/dt = -50\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$, $T_j = 25^\circ\text{C}$			115	ns
		$I_F = 1\text{ A}$, $di_F/dt = -100\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$, $T_j = 25^\circ\text{C}$		57	80	
		$I_F = 1\text{ A}$, $di_F/dt = -200\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$, $T_j = 25^\circ\text{C}$		45	65	
I_{RM}	Reverse recovery current	$I_F = 30\text{ A}$, $di_F/dt = -200\text{ A}/\mu\text{s}$, $V_R = 600\text{ V}$, $T_j = 125^\circ\text{C}$		25	35	A
S	Softness factor	$I_F = 30\text{ A}$, $di_F/dt = -200\text{ A}/\mu\text{s}$, $V_R = 600\text{ V}$, $T_j = 125^\circ\text{C}$		1.5		
t_{fr}	Forward recovery time	$I_F = 30\text{ A}$, $di_F/dt = 100\text{ A}/\mu\text{s}$, $V_{FR} = 1.5 \times V_{Fmax}$, $T_j = 25^\circ\text{C}$			550	ns
V_{FP}	Forward recovery voltage	$I_F = 30\text{ A}$, $di_F/dt = 100\text{ A}/\mu\text{s}$, $T_j = 25^\circ\text{C}$		6		V

Figure 1. Conduction losses versus average current

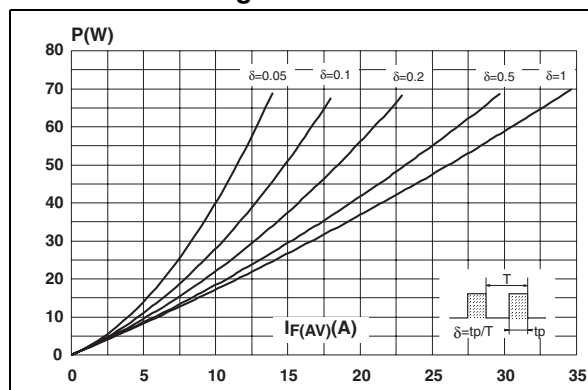


Figure 2. Forward voltage drop versus forward current

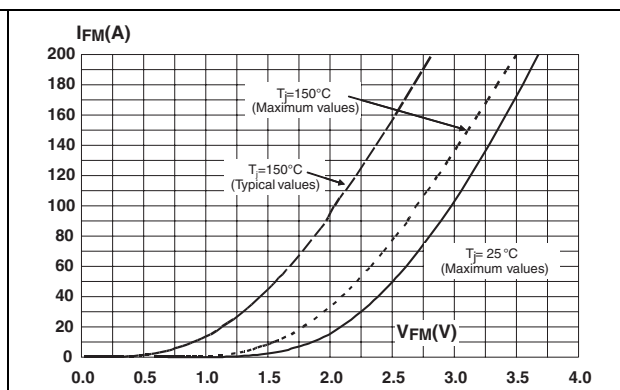


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

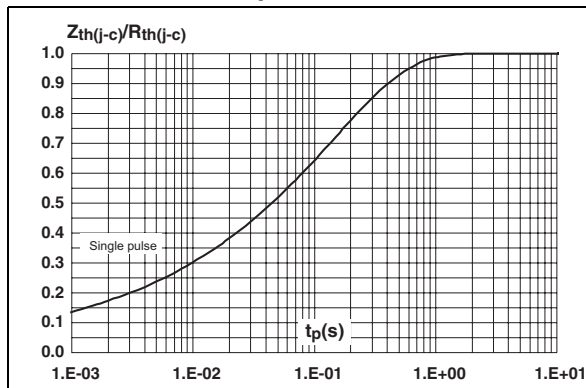


Figure 4. Peak reverse recovery current versus di_F/dt (typical values)

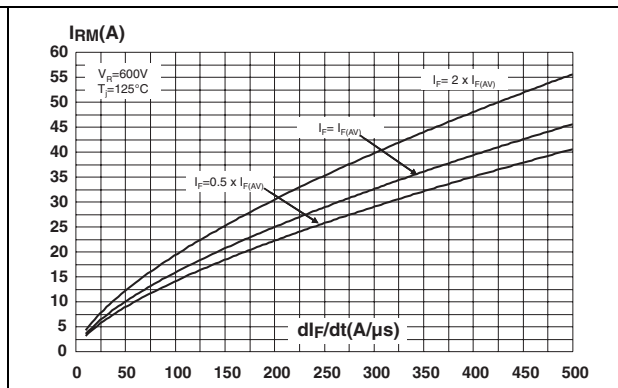


Figure 5. Reverse recovery time versus di_F/dt (typical values)

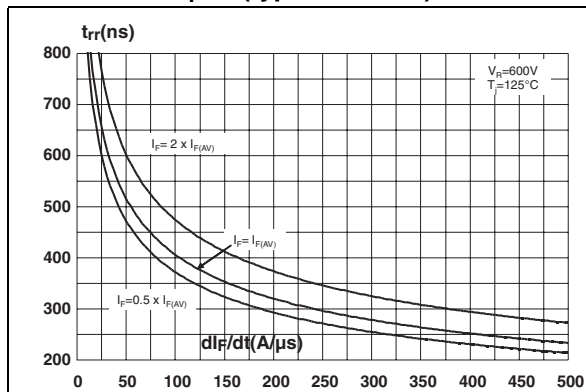


Figure 6. Reverse recovery charges versus di_F/dt (typical values)

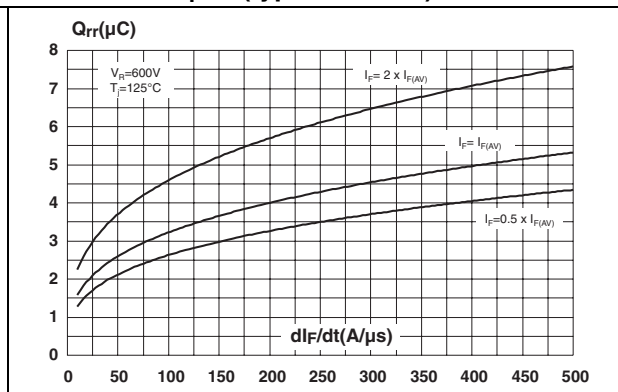


Figure 7. Softness factor versus di_F/dt (typical values)

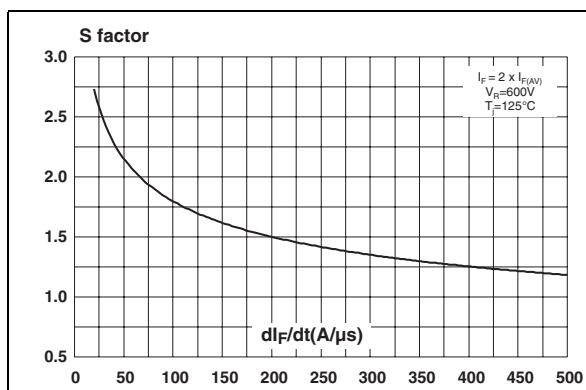


Figure 8. Relative variations of dynamic parameters versus junction temperature

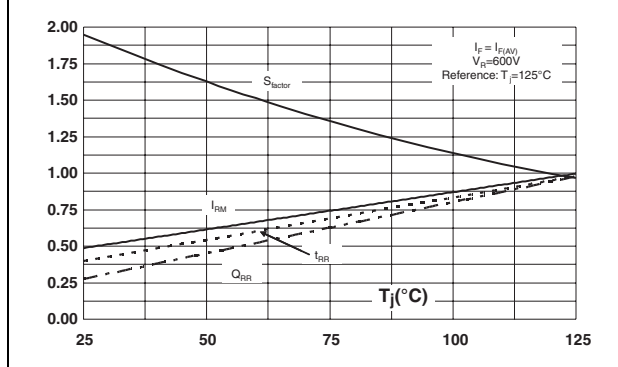


Figure 9. Transient peak forward voltage versus di_F/dt (typical values)

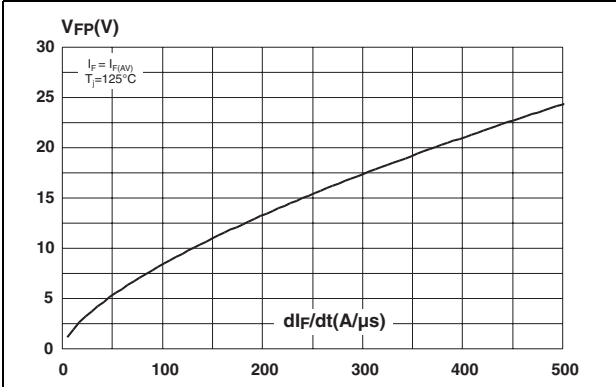


Figure 10. Forward recovery time versus di_F/dt (typical values)

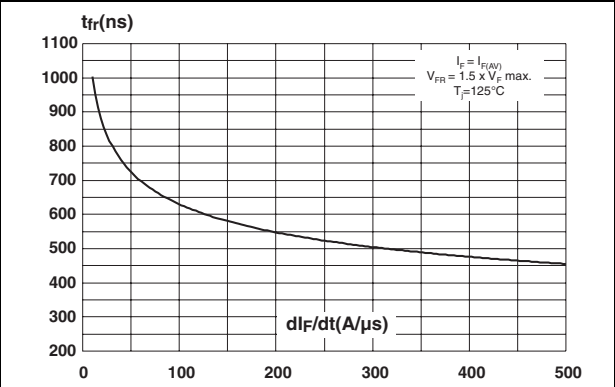
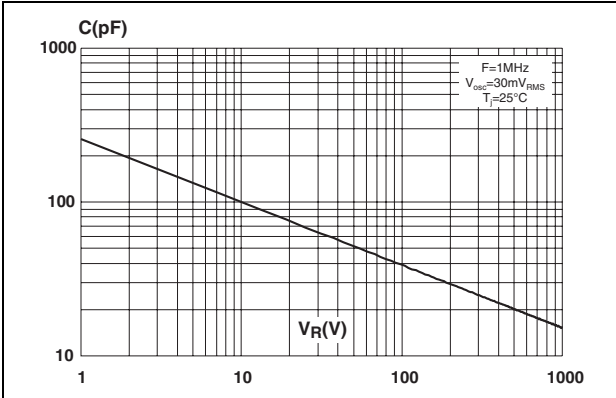


Table 5. Junction capacitance versus reverse voltage applied (typical values)



2 Package information

Epoxy meets UL94, V0

Cooling method: by conduction (C)

Table 6. ISOTOP dimensions

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max	Min.	Max.
A	11.80	12.20	0.465	0.480
A1	8.90	9.10	0.350	0.358
B	7.8	8.20	0.307	0.323
C	0.75	0.85	0.030	0.033
C2	1.95	2.05	0.077	0.081
D	37.80	38.20	1.488	1.504
D1	31.50	31.70	1.240	1.248
E	25.15	25.50	0.990	1.004
E1	23.85	24.15	0.939	0.951
E2	24.80 typ.		0.976 typ.	
G	14.90	15.10	0.587	0.594
G1	12.60	12.80	0.496	0.504
G2	3.50	4.30	0.138	0.169
F	4.10	4.30	0.161	0.169
F1	4.60	5.00	0.181	0.197
P	4.00	4.30	0.157	0.69
P1	4.00	4.40	0.157	0.173
S	30.10	30.30	1.185	1.193

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

3 Ordering information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
STTH6112TV1	STTH6112TV1	ISOTOP	27 g	10	Tube
STTH6112TV2	STTH6112TV2	ISOTOP	27 g	10	Tube

4 Revision history

Date	Revision	Description of Changes
02-Mar-2006	1	First issue.

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9